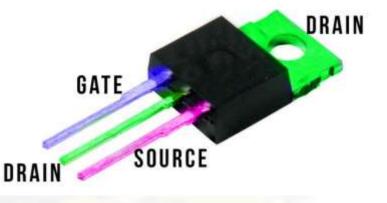


# UNIT IV



# METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTOR

S.JAYASHREEAP/EEE ECED-ICSE-C





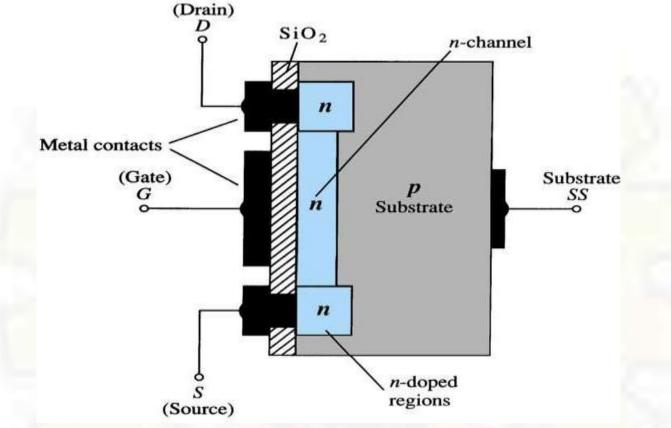


• There are 2 types of MOSFET's:

 Depletion mode MOSFET (D-MOSFET) N-channel D-Type MOSFET
P-channel D-Type MOSFET
Enhancement Mode MOSFET (E-MOSFET)

#### DEPLETION MODE MOSFET CONSTRUCTION



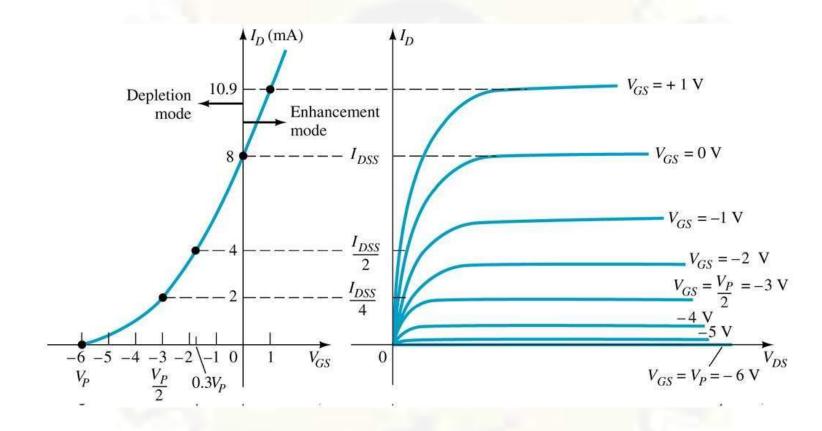


- The Drain (D) and Source (S) leads connect to the to n-doped regions
- These N-doped regions are connected by an n-channel
- This n-channel is connected to the Gate (G) via a thin insulating layer of SiO<sub>2</sub>
- The n-doped material lies on a p-doped substrate that may have an additional terminal connection called SS ECED-I CSE-C



## **BASIC OPERATION**





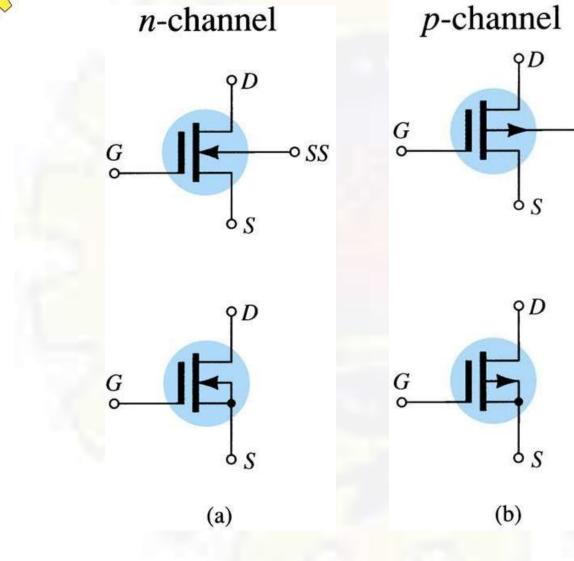
D-MOSFET may be biased to operate in two modes:The **Depletion** mode or The **Enhancement** mode



D-MOSFET Symbols



-o SS



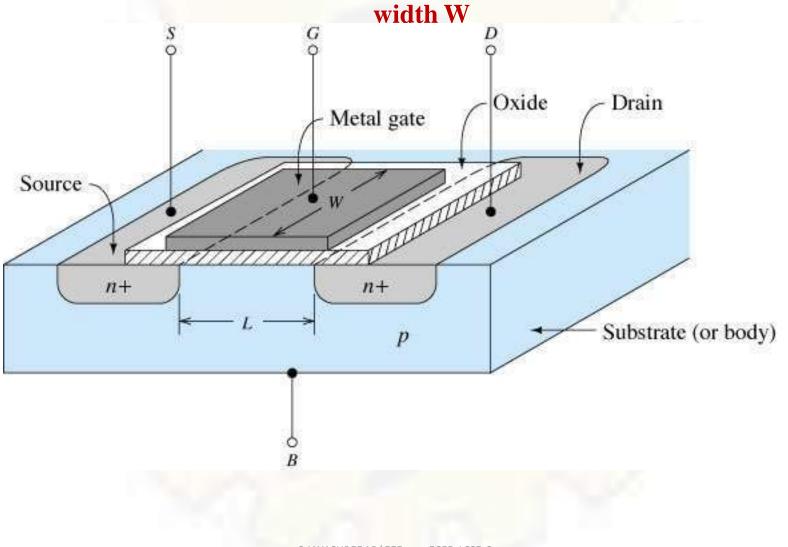


# ENHANCEMENT MODE MOSFET'S





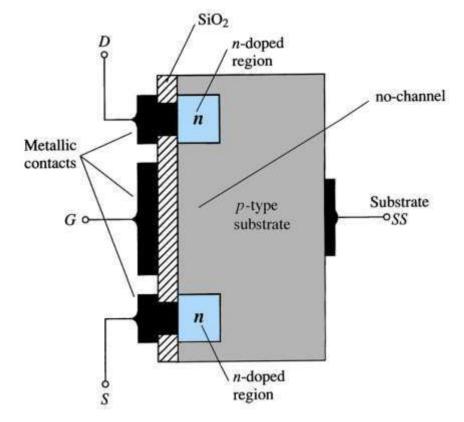
*n*-Channel E-MOSFET showing channel length L and channel





#### Enhancement Mode MOSFET Construction





The Drain (D) and Source (S) connect to the to n-doped regions

These n-doped regions are not connected via an n-channel without an external voltage

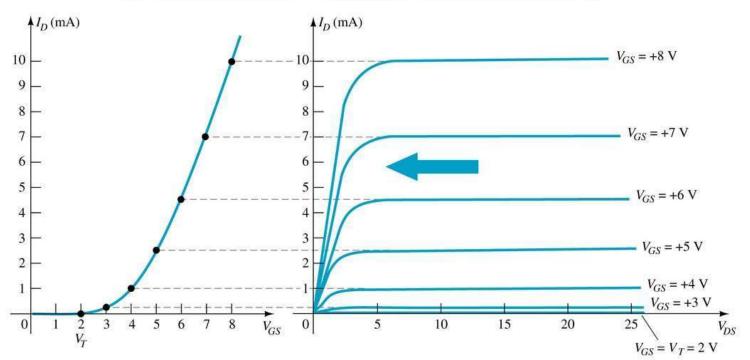
The Gate (G) connects to the p-doped substrate via a thin insulating layer of SiO<sub>2</sub> The n-doped material lies on a p-doped substrate that may have an additional terminal connection called SS



#### **Basic Operation**



The Enhancement mode MOSFET only operates in the enhancement mode.



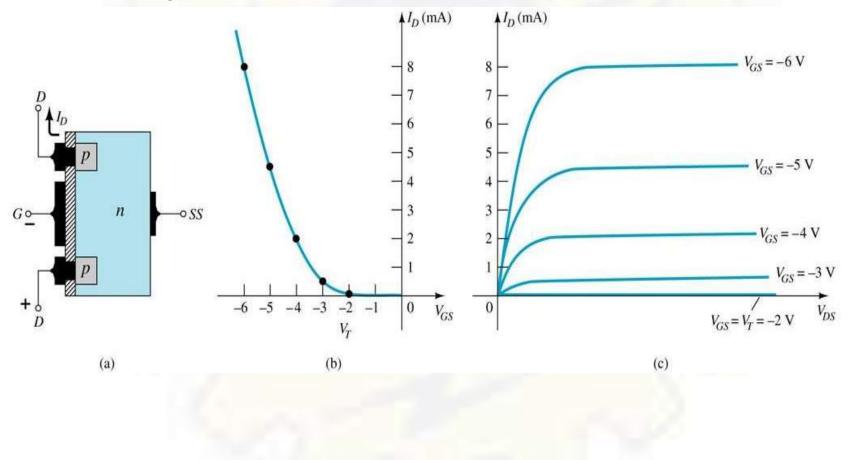
VGs is always positive IDSS = 0 when VGS < VT As VGs increases above VT, ID increases If VGs is kept constant and VDs is increased, then ID saturates (IDSS) The saturation level, VDSsat is reached.



#### p-Channel Enhancement Mode MOSFETs



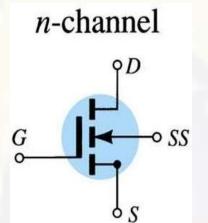
The p-channel Enhancement mode MOSFET is similar to the n-channel except that the voltage polarities and current directions are reversed.

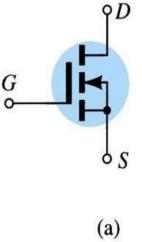




## E-MOSFET Symbols









## SOME PACKAGES OF MOSFET



